

❖ Recipe for SI Etch.

Substrate Temp.	Chamber servo pressure(mTorr)	Source power (w)	Bias Power(w)	Gases(scc)		Process Time	Etch rate
				CF4	CHF3		
Room Temp.	15	800	80	100	10	Max 15 mins.	-

❖ Recipe for SiO2Etch.

Substrate Temp.	Chamber servo pressure(mTorr)	Source power (w)	Bias Power(w)	Gases(scc)		Process Time	Etch rate
				CF4	CHF3		
Room Temp.	15	400	40	100	10	Max 15 mins.	-